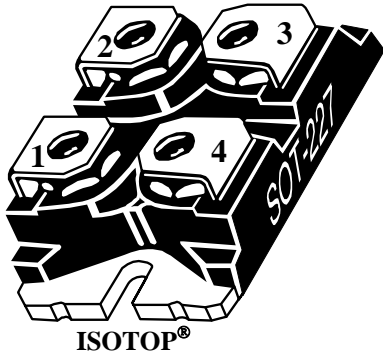
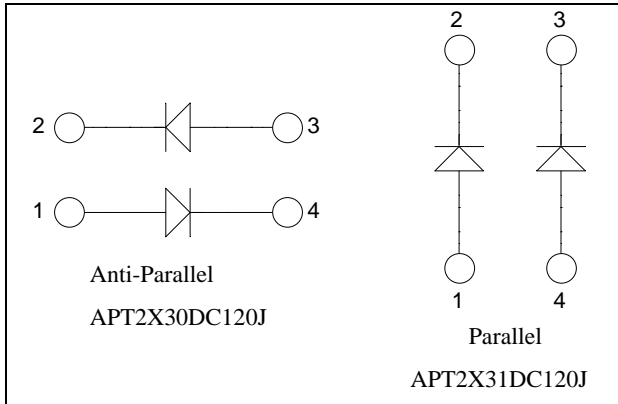


**ISOTOP<sup>®</sup> SiC Diode**  
**Power Module**
 $V_{RRM} = 1200V$   
 $I_F = 30A @ T_C = 100^{\circ}C$ 

**Application**

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

**Features**

- **SiC Schottky Diode**
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

**Absolute maximum ratings (per leg)**

Symbol	Parameter	Max ratings	Unit
$V_R$	Maximum DC reverse Voltage	1200	V
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward Current	30	A
$I_{FSM}$	Non-Repetitive Forward Surge Current		
		10 $\mu s$	$T_C = 25^{\circ}C$

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

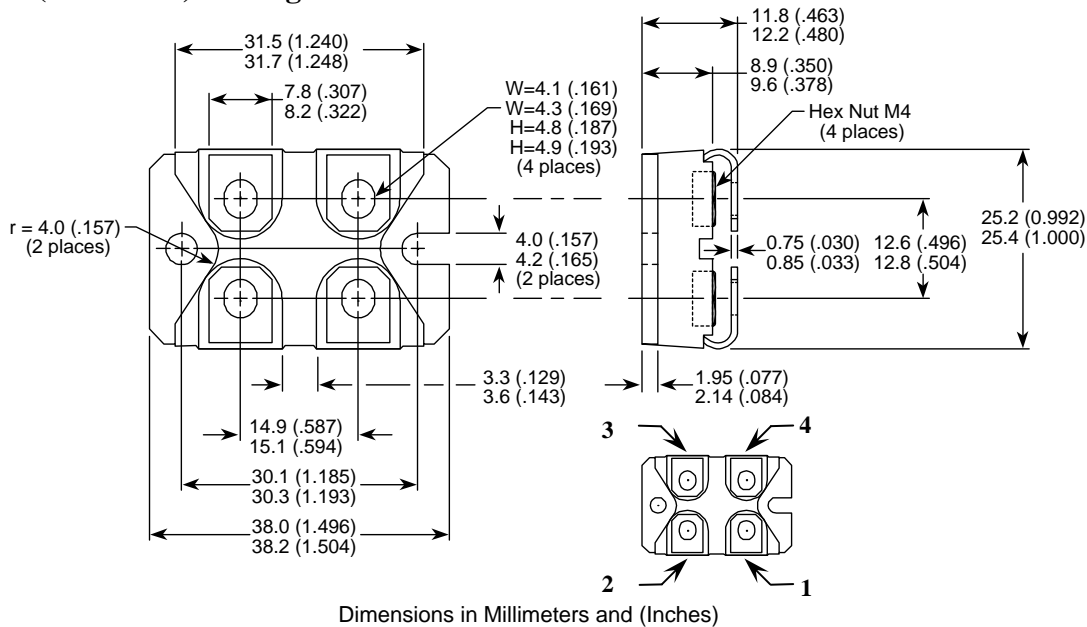
All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

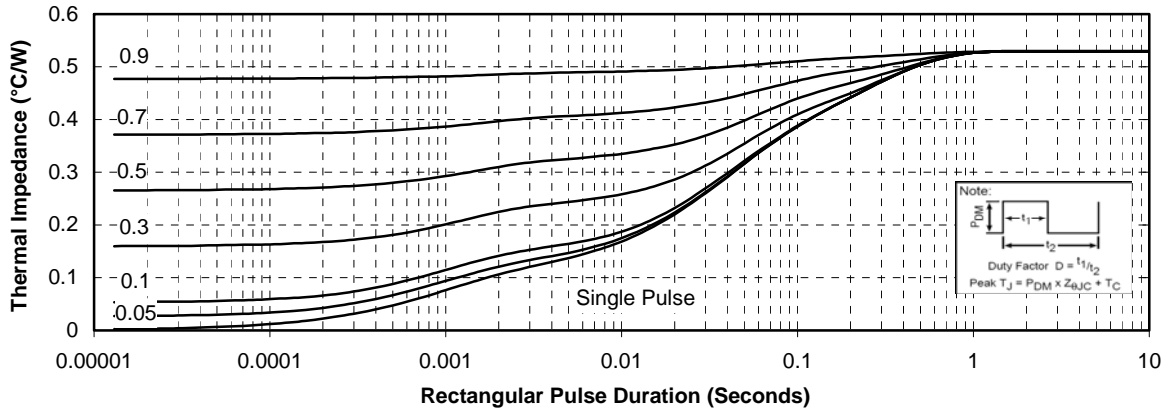
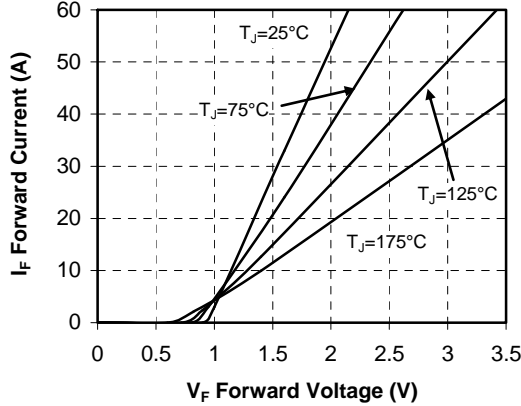
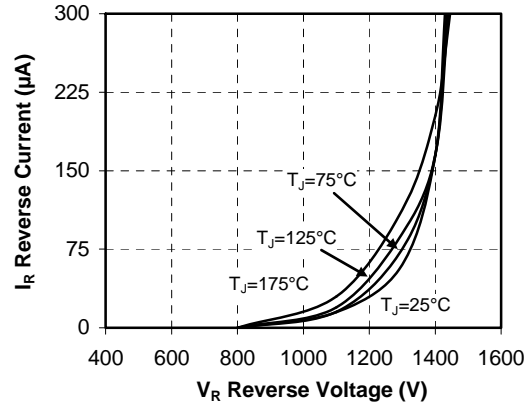
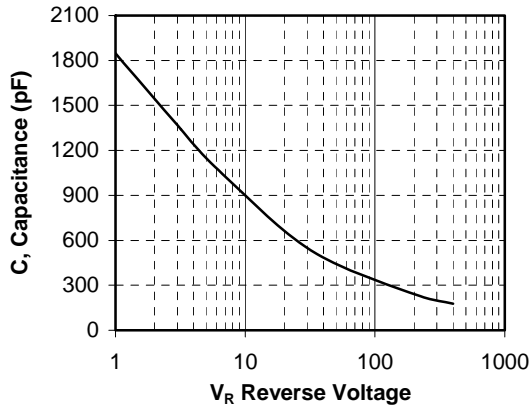
**Electrical Characteristics (per leg)**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$V_F$	Diode Forward Voltage	$I_F = 30\text{A}$	$T_j = 25^\circ\text{C}$		1.6	1.8	V
			$T_j = 175^\circ\text{C}$		2.3	3.0	
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		96	600	$\mu\text{A}$
			$T_j = 175^\circ\text{C}$		168	3000	
$Q_C$	Total Capacitive Charge	$I_F = 30\text{A}, V_R = 600\text{V}$ $di/dt = 1500\text{A}/\mu\text{s}$		120		nC	
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200\text{V}$		288		pF	
		$f = 1\text{MHz}, V_R = 400\text{V}$		207			

**Thermal and package characteristics (per leg)**

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal resistance			0.53	$^\circ\text{C}/\text{W}$
$R_{thJA}$	Junction to Ambient (IGBT & Diode)			20	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol} < 1\text{mA}$ , 50/60Hz	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-55		175	$^\circ\text{C}$
$T_L$	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

**SOT-227 (ISOTOP<sup>®</sup>) Package Outline**


**Typical Diode Performance Curve**
**Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration**

**Forward Characteristics**

**Reverse Characteristics**

**Capacitance vs. Reverse Voltage**


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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.